

Unbuffered Memory Module Data Sheet

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MW02GN1038UA8 / MW02GN1338UA8

2 GBytes, DDR3, PC3-8500 (1066 MHz) / PC3-10600 (1333 MHz) CL8 240 Pin Unbuffered DIMM

Description:

MW02GN1038UA8 and **MW02GN1338UA8** are 2 Gigabyte Memory Modules, organized as 256Mx64 bits DDR3-SDRAM. The modules are composed by sixteen 128Mx8 DDR3-SDRAMs ICs in FBGA package forming two logical banks and one serial EEPROM for SPD (Serial Presence Detect), mounted on a JEDEC-Standard 240-pin DIMM (Dual In Line Memory Module) with golden contacts.

Features:

- Component JEDEC speed bin (CL-t_{RCD}-t_{RP}) DDR3-(8-8-8)
- 240-pin DIMM outline, unbuffered
- Dual Bank Memory Modules — Use 128Mx8 DDR3 SDRAMs
- Double Data Rate architecture; two data transfers per clock cycle
- On-Die Termination Control (ODT)
- Differential clock inputs
- Burst length (BL): 8 and 4 with Burst Chop (BC)
- Clock Cycle Time (t_{CK} avg) @ CL = 8:
 - MW02GN1338UA8: 1.50 ns
 - MW02GN1038UA8: 1.875 ns
- EEPROM Serial Presence Detection (SPD)
- Bidirectional, differential data strobe (DQS and /DQS)
- Eight internal device banks for concurrent operation
- Refresh to Active (t_{RFC}): 110 ns (min)
- Auto precharge option for each burst access
- Auto-refresh and Self-refresh modes
- Row address A₀-A₁₃
- Column address A₀-A₉
- Bank address: BA₀~BA₂
- SSTL_15 Interface: VDD = 1.5 V ± 0.075 V
- Refresh period (see note 6 below):
 - 0°C ≤ TC ≤ +85°C : 7.8 μs
 - +85°C < TC ≤ +95°C: 3.9 μs

DC Characteristics

(TC=0°C to +85°C, VDD, VDDQ = 1.5V± 0.075V)

| Parameter <small>(NOTE: Since each bank can be in a different mode, data reflect current consumption PER BANK)</small> | Symbol | MW02GN1038UA8 | MW02GN1338UA8 | Unit | Notes |
|---|--------|---------------|---------------|------|---|
| | | max. | max. | | |
| Operating Current (ACT=PRE) | IDD0 | 680 | 760 | mA | |
| Operating Current (ACT-READ-PRE) | IDD1 | 800 | 880 | mA | |
| Precharge Power Down Standby Current | IDD2P1 | 280 | 320 | mA | Fast PD exit Slow PD exit |
| | IDD2P0 | 104 | 112 | mA | |
| Precharge Quiet Standby Current | IDD2Q | 440 | 480 | mA | |
| Precharge Standby Current | IDD2N | 440 | 480 | mA | |
| Active Power-Down Current | IDD3P | 280 | 320 | mA | Always Fast exit |
| Active Standby Current | IDD3N | 480 | 520 | mA | |
| Operating Current | IDD4R | 1280 | 1600 | mA | Burst Read operating Burst Write operating |
| | IDD4W | 1360 | 1680 | mA | |
| Burst refresh Current | IDD5B | 2080 | 2160 | mA | |
| All Bank Interleave read current | IDD7R | 2160 | 2480 | mA | |

Recommended DC Operating Conditions:

(TC = 0°C to +85°C) ⁶

| Parameter | Symbol | min. | typ. | max. | Unit | Notes |
|--------------------------------|-------------|-------------|-------------|-------------|------|---------|
| Supply Voltage | VDD, VDDQ | 1.425 | 1.5 | 1.575 | V | 1,2,3 |
| | VSS | 0 | 0 | 0 | V | 1 |
| | VDDSPD | 3.0 | 3.3 | 3.6 | V | |
| Input Reference Voltage | VREFCA (DC) | 0.49 x VDD | 0.50 x VDD | 0.51 x VDD | V | 1, 4, 5 |
| Input Reference Voltage for DQ | VREFDQ (DC) | 0.49 x VDDQ | 0.50 x VDDQ | 0.51 x VDDQ | V | 1, 4, 5 |

AC Characteristics:

(TC=0°C to +85°C, VDD, VDDQ = 1.5V± 0.075V, VSS, VSSQ = 0V)

| Parameter | MW02GN1038UA8 | | MW02GN1338UA8 | | Unit (Notes) |
|-----------------------------|---------------|-----------|---------------|-----------|--------------|
| | min. | max. | min. | max. | |
| tAA | 15 | 20 | 12 | 20 | ns |
| tWR | 15 | - | 15 | - | ns |
| tRCD | 15 | - | 12 | - | ns |
| tRRD | 7.5 | - | 6 | - | ns |
| | 4 | - | 4 | - | nCK |
| tRP | 15 | - | 12 | - | ns |
| tRAS | 37.5 | 9 x tREFI | 36 | 9 x tREFI | ns (7) |
| tRC | 52.50 | - | 48.0 | - | ns |
| tRFC | 110 | - | 110 | - | ns |
| tWTR | 7.5 | - | 7.5 | - | ns |
| | 4 | - | 4 | - | nCK |
| tRTP | 7.5 | - | 7.5 | - | ns |
| | 4 | - | 4 | - | nCK |
| tFAW | 37.5 | - | 30 | - | ns |
| tREFI | - | 7.8 | - | 7.8 | μS (6, 7) |
| tREFI +85°C ≤ TC ≤ +95°C | - | 3.9 | - | 3.9 | μS (6, 7) |

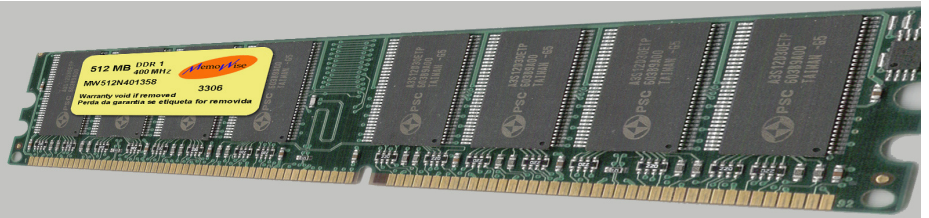
Notes:

1. DDR3 SDRAM Component Specification
2. Under all conditions VDDQ must be less than or equal to VDD.
3. VDDQ tracks with VDD. AC parameters are measured with VDD and VDDQ tied together
4. The AC peak noise on VREF may not allow VREF to deviate from VREF (DC) by more than ±1% VDD (for reference: approx. ±15 mV)
5. For reference: approx. VDD/2 ±15
6. When operating in the Range +85°C ~ +95°C (TC = temperature of the DRAM ICs case) the following must be observed:
 - a. Refresh commands must be issued at double frequency, thus t_{REF} must be lowered to 3.9μs
 - b. If Self-Refresh must be used, it is mandatory to either use Manual Self-Refresh with Extended Temperature Range Capability (MR2 bits [A6, A7] = [0, 1]) or Auto Self Refresh Mode must be enabled (MR2 bits [A6, A7] = [1, 0]).
7. tREFI depends on operating case temperature (TC)

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Dimensions

All dimensions are in millimeters
Tolerance is $\pm 0.1\text{mm}$ unless otherwise indicated

